

# PNP RF Transistor MMBTH81

This device is designed for general RF amplifier and mixer applications to 250 MHz with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 75.

#### **Features**

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements;
   AEC-Q101 Qualified and PPAP Capable

#### **MAXIMUM RATINGS** (T<sub>A</sub> = 25°C unless otherwise noted)

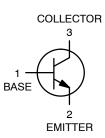
Rating	Symbol	Value	Units
Collector - Emitter Voltage	V <sub>CEO</sub>	20	V
Collector - Base Voltage	V <sub>CBO</sub>	20	V
Emitter - Base Voltage	V <sub>EBO</sub>	3.0	V
Collector Current - Continuous	I <sub>C</sub>	50	mA
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### **THERMAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Max	Unit
Total Device Dissipation Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Device mounted on FR-4 PCB  $1.6 \times 1.6 \times 0.06$  in.
- 2. These ratings are based on a maximum junction temperature of 150°C.
- 3. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 4. All voltages (V) and currents (A) are negative polarity for PNP transistors.





SOT-23 CASE 318-08 STYLE 6

#### **MARKING DIAGRAM**



3D = Specific Device Code

M = Date Code\*

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### MMBTH81

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter Test Conditions		Min	Max	Units	
OFF CHARACTERISTICS						
V <sub>(BR)CEO</sub>	Collector - Emitter Breakdown Voltage (Note 5)	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0	20		V	
V <sub>(BR)CBO</sub>	Collector - Base Breakdown Voltage	I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0	20		V	
V <sub>(BR)EBO</sub>	Emitter – Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	3.0		V	
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0		100	nA	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 2.0 V, I <sub>C</sub> = 0		100	nA	
ON CHARAC	CTERISTICS					
h <sub>FE</sub>	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$	60			
V <sub>CE(sat)</sub>	Collector - Emitter Saturation Voltage	$I_C = 5.0 \text{ mA}, I_B = 0.5 \text{ mA}$		0.5	V	
V <sub>BE(sat)</sub>	Base - Emitter Saturation Voltage	I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V		0.9	V	
SMALL SIGN	NAL CHARACTERISTICS					
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 100 \text{ MHz}$	600		MHz	
C <sub>cb</sub>	Collector-Base Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		0.85	pF	
C <sub>ce</sub>	Collector Emitter Capacitance	V <sub>CB</sub> = 10 V, I <sub>B</sub> = 0, f = 1.0 MHz		0.65	pF	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

### SPICE MODEL

PNP(Is=10f Xti=3 Eg=1.11 Vaf=100 Bf=133.8 Ise=1.678p Ne=2.159 Ikf=.1658 Nk=.901 Xtb=1.5 Var=100 Br=1 Isc=9.519n Nc=3.88 Ikr=5.813 Rc=7.838 Cjc=2.81p Mjc=.1615 Vjc=.8282 Fc=.5 Cje=2.695p Mje=.3214 Vje=.7026 Tr=11.32n Tf=97.83p Itf=69.29 Xtf=599u Vtf=10)

#### **ORDERING INFORMATION**

Device	Specific Marking Code	Package	Shipping <sup>†</sup>
NSVMMBTH81LT1G*	3D	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTH81LT3G*	3D	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

#### MMBTH81

#### **TYPICAL CHARACTERISTICS**

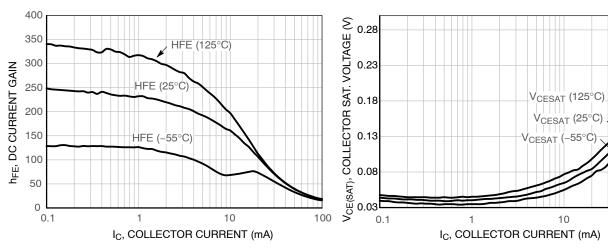


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Saturation Voltage vs. **Collector Current** 

100

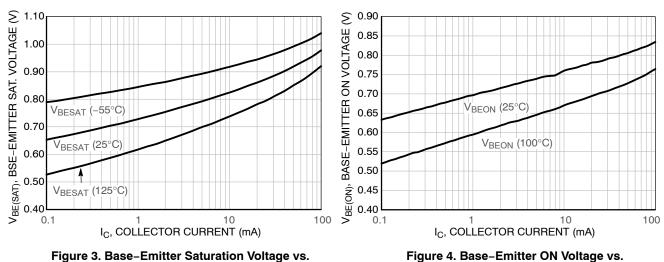


Figure 3. Base-Emitter Saturation Voltage vs. **Collector Current** 

**Collector Current** 

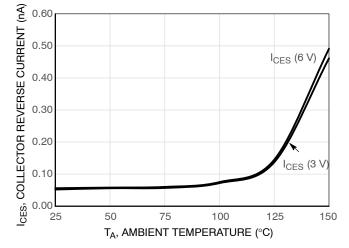


Figure 5. Collector Reverse Current vs. **Ambient Temperature** 

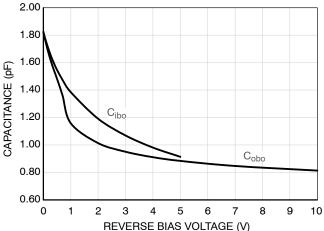


Figure 6. Input /Output Capacitance vs. **Reverse Bias Voltage** 

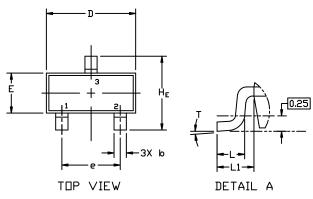


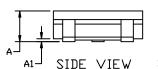


**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

## GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



#### **SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

## **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## onsemi

NSVMMBTH81LT1G NSVMMBTH81LT3G